

TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
µPOWER OPERATIONAL AMPLIFIERS
 SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

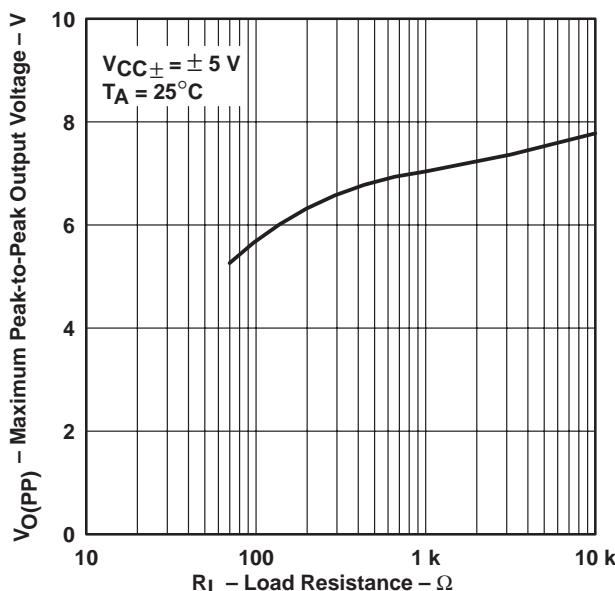
- **Excellent Output Drive Capability**
 $V_O = \pm 2.5 \text{ V Min at } R_L = 100 \Omega,$
 $V_{CC\pm} = \pm 5 \text{ V}$
 $V_O = \pm 12.5 \text{ V Min at } R_L = 600 \Omega,$
 $V_{CC\pm} = \pm 15 \text{ V}$
- **Low Supply Current . . . 280 µA Typ**
- **Decompensated for High Slew Rate and Gain-Bandwidth Product**
 $A_{VD} = 0.5 \text{ Min}$
Slew Rate = 10 V/µs Typ
Gain-Bandwidth Product = 6.5 MHz Typ
- **Wide Operating Supply Voltage Range**
 $V_{CC\pm} = \pm 3.5 \text{ V to } \pm 18 \text{ V}$
- **High Open-Loop Gain . . . 280 V/mV Typ**
- **Low Offset Voltage . . . 500 µV Max**
- **Low Offset Voltage Drift With Time**
 $0.04 \mu\text{V/Month Typ}$
- **Low Input Bias Current . . . 5 pA Typ**

description

The TLE2161, TLE2161A, and TLE2161B are JFET-input, low-power, precision operational amplifiers manufactured using the Texas Instruments Excalibur process. Decompensated for stability with a minimum closed-loop gain of 5, these devices combine outstanding output drive capability with low power consumption, excellent dc precision, and high gain-bandwidth product.

In addition to maintaining the traditional JFET advantages of fast slew rates and low input bias and offset currents, the Excalibur process offers outstanding parametric stability over time and temperature. This results in a device that remains precise even with changes in temperature and over years of use.

**MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE
vs
LOAD RESISTANCE**



AVAILABLE OPTIONS

TA	VIOMAX AT 25°C	PACKAGE			
		SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (JG)	PLASTIC DIP (P)
0°C to 70°C	500 µV 1.5 mV 3 mV	TLE2161ACD TLE2161CD	—	—	TLE2161BCP TLE2161ACP TLE2161CP
-40°C to 85°C	500 µV 1.5 mV 3 mV	— TLE2161AID TLE2161ID	—	—	TLE2161BIP TLE2161AIP TLE2161IP
-55°C to 125°C	500 µV 1.5 mV 3 mV	— TLE2161AMD TLE2161MD	— TLE2161AMFK TLE2161MFK	TLE2161BMJG TLE2161AMJG TLE2161MJG	TLE2161BMP TLE2161AMP TLE2161MP

The D packages are available taped and reeled. Add R suffix to device type (e.g., TLE2161ACDR).



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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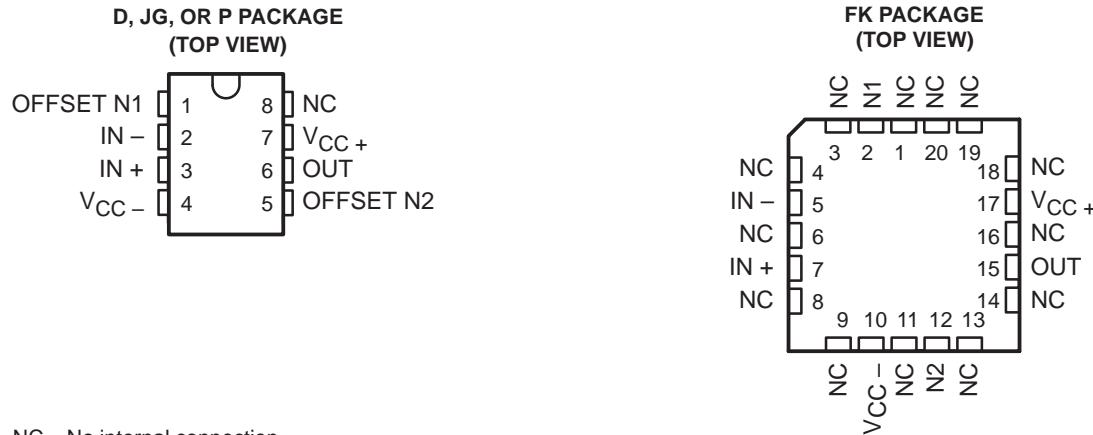
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SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

description (continued)

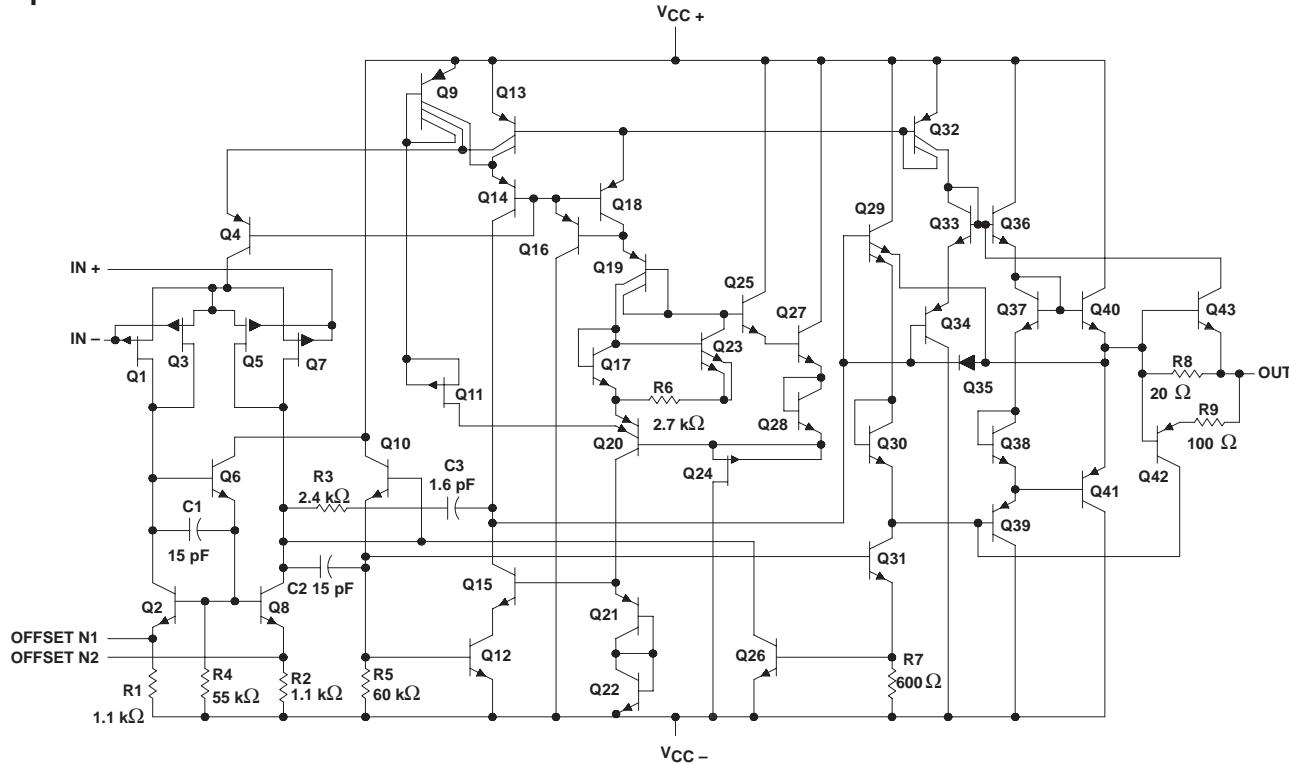
A variety of available options includes small-outline packages and chip-carrier versions for high-density system applications.

The C-suffix devices are characterized for operation from 0°C to 70°C. The I-suffix devices are characterized for operation from -40°C to 85°C. The M-suffix devices are characterized for operation over the full military temperature range of -55°C to 125°C.



NC – No internal connection

equivalent schematic



All component values are nominal.

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V_{CC+} (see Note 1)	19 V
Supply voltage, V_{CC-}	-19 V
Differential input voltage, V_{ID} (see Note 2)	±38 V
Input voltage range, V_I (any input)	$V_{CC\pm}$
Input current, I_I (each input)	±1 mA
Output current, I_O	±80 mA
Total current into V_{CC+}	80 mA
Total current out of V_{CC-}	80 mA
Duration of short-circuit current at (or below) 25°C (see Note 3)	unlimited
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T_A :	C suffix	0°C to 70°C
	I suffix	-40°C to 85°C
	M suffix	-55°C to 125°C
Storage temperature range, T_{STG}	-65°C to 150°C
Case temperature for 60 seconds: FK package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D or P package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: JG package	300°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to the midpoint between V_{CC+} and V_{CC-} .
 2. Differential voltages are at IN+ with respect to IN-.
 3. The output may be shorted to either supply. Temperature and /or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ C$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ C$	$T_A = 70^\circ C$ POWER RATING	$T_A = 85^\circ C$ POWER RATING	$T_A = 125^\circ C$ POWER RATING
D	725 mW	5.8 mW/ $^\circ C$	464 mW	377 mW	145 mW
FK	1375 mW	11.0 mW/ $^\circ C$	880 mW	715 mW	275 mW
JG	1050 mW	8.4 mW/ $^\circ C$	672 mW	546 mW	210 mW
P	1000 mW	8.0 mW/ $^\circ C$	640 mW	520 mW	200 mW

recommended operating conditions

	C SUFFIX		I SUFFIX		M SUFFIX		UNIT
	MIN	MAX	MIN	MAX	MIN	MAX	
Supply voltage, $V_{CC\pm}$	±3.5	±18	±3.5	±18	+3.5	±18	V
Common-mode input voltage, V_{IC}	$V_{CC\pm} = \pm 5 V$	-1.6	4	-1.6	4	-1.6	4
	$V_{CC\pm} = \pm 15 V$	-11	13	-11	13	-11	13
Operating free-air temperature, T_A	0	70	-40	85	-55	125	°C



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SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

electrical characteristics at specified free-air temperature, $V_{CC \pm} = \pm 5$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A^\dagger	TLE2161C, TLE2161AC TLE2161BC			UNIT	
				MIN	TYP	MAX		
V_{IO}	Input offset voltage	$V_{IC} = 0$, $R_S = 50 \Omega$	25°C	0.8	3.1		mV	
			Full range		4			
			25°C	0.6	2.6			
	TLE2161AC		Full range		3.5			
			25°C	0.5	1.9			
			Full range		2.4			
	TLE2161BC		Full range	6		$\mu\text{V}/^\circ\text{C}$		
			25°C	0.04		$\mu\text{V}/\text{mo}$		
			25°C	1		pA		
αV_{IO}	Temperature coefficient of input offset voltage		Full range		0.8	nA		
	Input offset voltage long-term drift (see Note 4)		25°C	3		pA		
	I_{IO}		Full range		2	nA		
	I_{IB}		25°C	3		pA		
V_{ICR}	Common-mode input voltage range		25°C	-1.6 to 4	-2 to 6		V	
			Full range	-1.6 to 4			V	
V_{OM+}	Maximum positive peak output voltage swing	$R_L = 10 \text{ k}\Omega$	25°C	3.5	3.7		V	
			Full range	3.3				
		$R_L = 100 \Omega$	25°C	2.5	3.1			
			Full range	2				
V_{OM-}	Maximum negative peak output voltage swing	$R_L = 10 \text{ k}\Omega$	25°C	-3.7	-3.9		V	
			Full range	-3.3				
		$R_L = 100 \Omega$	25°C	-2.5	-2.7			
			Full range	-2				
AVD	Large-signal differential voltage amplification	$V_O = \pm 2.8 \text{ V}, R_L = 10 \text{ k}\Omega$	25°C	15	80		V/mV	
			Full range	2				
		$V_O = 0 \text{ to } 2 \text{ V}, R_L = 100 \Omega$	25°C	0.75	45			
			Full range	0.5				
		$V_O = 0 \text{ to } -2 \text{ V}, R_L = 100 \Omega$	25°C	0.5	3			
			Full range	0.25				
r_i	Input resistance		25°C	1012		Ω		
c_i	Input capacitance		25°C	4		pF		
z_o	Open-loop output impedance	$I_O = 0$	25°C	280		Ω		
CMRR	Common-mode rejection ratio	$V_{IC}=V_{ICR\min}, R_S = 50 \Omega$	25°C	65	82		dB	
			Full range	65				
kSVR	Supply-voltage rejection ratio ($\Delta V_{CC\pm} / \Delta V_{IO}$)	$V_{CC\pm} = \pm 5 \text{ V to } \pm 15 \text{ V}, R_S = 50 \Omega$	25°C	75	93		dB	
			Full range	75				
I_{CC}	Supply current	$V_O = 0$, No load	25°C	280	325		μA	
			Full range		350			
	ΔI_{CC}		Full range		29			

† Full range is 0°C to 70°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



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 SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

operating characteristics at specified free-air temperature, $V_{CC} \pm = \pm 5$ V (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A \dagger$	TLE2161C, TLE2161AC TLE2161BC			UNIT
			MIN	TYP	MAX	
			25°C	7	10	
SR	Slew rate (see Figure 1) $A_{VD} = 5$, $R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	Full range	5			$\text{V}/\mu\text{s}$
V_n	Equivalent input noise voltage (see Figure 2) $R_S = 20 \Omega$, $f = 10 \text{ Hz}$ $R_S = 20 \Omega$, $f = 1 \text{ kHz}$	25°C		59	100	$\text{nV}/\sqrt{\text{Hz}}$
				43	60	
$V_n(\text{PP})$	Peak-to-peak equivalent input noise voltage $f = 0.1 \text{ Hz to } 10 \text{ Hz}$	25°C		1.1		μV
I_n	Equivalent input noise current $f = 1 \text{ kHz}$	25°C		1		$\text{fA}/\sqrt{\text{Hz}}$
THD	Total harmonic distortion $V_O(\text{PP}) = 2 \text{ V}$, $A_{VD} = 5$, $f = 10 \text{ kHz}$, $R_L = 10 \text{ k}\Omega$	25°C		0.025%		
Gain-bandwidth product (see Figure 3)	$f = 100 \text{ kHz}$, $R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	25°C		5.8		MHz
	$f = 100 \text{ kHz}$, $R_L = 100 \text{ k}\Omega$, $C_L = 100 \text{ pF}$			4.3		
t_s	Settling time $\varepsilon = 0.1\%$ $\varepsilon = 0.01\%$	25°C		5		μs
				10		
B_{OM}	Maximum output-swing bandwidth $A_{VD} = 5$, $R_L = 10 \text{ k}\Omega$	25°C		420		kHz
ϕ_m	Phase margin (see Figure 3) $A_{VD} = 5$, $R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$ $A_{VD} = 5$, $R_L = 100 \Omega$, $C_L = 100 \text{ pF}$	25°C		70°		
				84°		

† Full range is 0°C to 70°C.

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SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

electrical characteristics at specified free-air temperature, $V_{CC} = \pm 15$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A^\dagger	TLE2161C, TLE2161AC TLE2161BC			UNIT		
				MIN	TYP	MAX			
V_{IO}	Input offset voltage	$V_{IC} = 0$, $R_S = 50\Omega$	25°C	0.6	3		mV		
			Full range		3.9				
			25°C	0.5	1.5				
	TLE2161AC		Full range		2.5				
			25°C	0.3	0.5				
	TLE2161BC		Full range		1				
			Full range	6		$\mu\text{V}/^\circ\text{C}$			
			25°C	0.04		$\mu\text{V}/\text{mo}$			
			25°C	2		pA			
			Full range		1	nA			
I_{IO}	Input offset current		25°C	4		pA	pA		
			Full range		3	nA			
	I_{IB}		25°C	–11	–12		V		
			Full range	–11	to 13		V		
V_{ICR}	Common-mode input voltage range		$R_L = 10\text{ k}\Omega$	25°C	13.2	13.7	V		
				Full range	13				
	V_{OM+}			25°C	12.5	13.2			
				Full range	12				
V_{OM-}	Maximum negative peak output voltage swing		$R_L = 10\text{ k}\Omega$	25°C	–13.2	–13.7	V		
				Full range	–13				
				25°C	–12.5	–13			
				Full range	–12				
AVD	Large-signal differential voltage amplification		$V_O = \pm 10\text{ V}$, $R_L = 10\text{ k}\Omega$	25°C	30	230	V/mV		
				Full range	20				
			$V_O = 0$ to 8 V , $R_L = 600\Omega$	25°C	25	100			
				Full range	10				
			$V_O = 0$ to $–8\text{ V}$, $R_L = 600\Omega$	25°C	3	25			
				Full range	1				
r_i	Input resistance			25°C		10^{12}	Ω		
c_i	Input capacitance			25°C		4	pF		
z_o	Open-loop output impedance	$I_O = 0$		25°C		280	Ω		
CMRR	Common-mode rejection ratio		$V_{IC} = V_{ICR\text{min}}$, $R_S = 50\Omega$	25°C	72	90	dB		
				Full range	70				
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm} / \Delta V_{IO}$)		$V_{CC\pm} = \pm 5\text{ V}$ to $\pm 15\text{ V}$, $R_S = 50\Omega$	25°C	75	93	dB		
				Full range	75				
I_{CC}	Supply current		$V_O = 0$, No load	25°C	290	350	μA		
				Full range		375			
	ΔI_{CC}			Full range		34			

† Full range is 0°C to 70°C .

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



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operating characteristics at specified free-air temperature, $V_{CC\pm} = \pm 15$ V (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T_A^\dagger	TLE2161C, TLE2161AC TLE2161BC			UNIT
			MIN	TYP	MAX	
SR	Slew rate (see Figure 1)	$A_VD = 5, R_L = 10 \text{ k}\Omega, C_L = 100 \text{ pF}$	25°C	7	10	$\text{V}/\mu\text{s}$
			Full range	5		
V_n	Equivalent input noise voltage (see Figure 2)	$R_S = 20 \Omega, f = 10 \text{ Hz}$	25°C	70	100	$\text{nV}/\sqrt{\text{Hz}}$
		$R_S = 20 \Omega, f = 1 \text{ kHz}$		40	60	
$V_{n(PP)}$	Peak-to-peak equivalent input noise voltage	$f = 0.1 \text{ Hz to } 10 \text{ Hz}$	25°C	1.1		μV
I_n	Equivalent input noise current	$f = 1 \text{ kHz}$	25°C	1.1		$\text{fA}/\sqrt{\text{Hz}}$
THD	Total harmonic distortion	$V_{O(PP)} = 2 \text{ V}, A_VD = 5, f = 10 \text{ kHz}, R_L = 10 \text{ k}\Omega$	25°C	0.025%		
	Gain-bandwidth product (see Figure 3)	$f = 100 \text{ kHz}, R_L = 10 \text{ k}\Omega, C_L = 100 \text{ pF}$	25°C	6.4		MHz
		$f = 100 \text{ kHz}, R_L = 600 \Omega, C_L = 100 \text{ pF}$		5.6		
t_s	Settling time	$\epsilon = 0.1\%$	25°C	5		μs
		$\epsilon = 0.01\%$		10		
B_{OM}	Maximum output-swing bandwidth	$A_VD = 5, R_L = 10 \text{ k}\Omega$	25°C	116		kHz
ϕ_m	Phase margin (see Figure 3)	$A_VD = 5, R_L = 10 \text{ k}\Omega, C_L = 100 \text{ pF}$	25°C	72°		
		$A_VD = 5, R_L = 600 \Omega, C_L = 100 \text{ pF}$		78°		

† Full range is 0°C to 70°C.

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electrical characteristics at specified free-air temperature, $V_{CC} \pm = \pm 5$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A^\dagger	TLE2161I, TLE2161AI TLE2161BI			UNIT	
				MIN	TYP	MAX		
V_{IO}	Input offset voltage	$V_{IC} = 0$, $R_S = 50\Omega$	25°C	0.8	3.1		mV	
			Full range		4.4			
			25°C	0.6	2.6			
	TLE2161AI		Full range		3.9			
			25°C	0.5	1.9			
			Full range		2.7			
αV_{IO}	Temperature coefficient of input offset voltage		Full range	6		$\mu V/^\circ C$		
Input offset voltage long-term drift (see Note 4)			25°C	0.04		$\mu V/mo$		
I_{IO}	Input offset current		25°C	1		pA	nA	
			Full range		2			
	Input bias current		25°C	3		pA		
			Full range		4	nA		
V_{ICR}	Common-mode input voltage range		25°C	-1.6 to 4	-2 to 6		V	
			Full range	-1.6 to 4				
			25°C	3.5	3.7			
			Full range	3.1				
$V_{OM} +$	Maximum positive peak output voltage	$R_L = 10\text{ k}\Omega$	25°C	2.5	3.1		V	
			Full range	2				
		$R_L = 100\Omega$	25°C	-3.7	-3.9			
			Full range	-3.1				
$V_{OM} -$	Maximum negative peak output voltage swing	$R_L = 10\text{ k}\Omega$	25°C	-2.5	-2.7		V	
			Full range	-2				
		$R_L = 100\Omega$	25°C	0.75	45			
			Full range	0.5				
A_{VD}	Large-signal differential voltage amplification	$V_O = \pm 2.8\text{ V}, R_L = 10\text{ k}\Omega$	25°C	0.5	3		V/mV	
			Full range	0.25				
		$V_O = 0$ to $2\text{ V}, R_L = 100\Omega$	25°C	15	80			
			Full range	2				
r_i	Input resistance	$V_O = 0$ to $-2\text{ V}, R_L = 100\Omega$	25°C	0.75	45		V/mV	
			Full range	0.5				
			25°C	0.5	3			
			Full range	0.25				
c_i	Input capacitance		25°C	1012		Ω		
z_0	Open-loop output impedance		25°C	4		pF		
CMRR	Common-mode rejection ratio		25°C	280		Ω	dB	
			Full range	280				
kSVR	Supply-voltage rejection ratio ($\Delta V_{CC} \pm / \Delta V_{IO}$)	$V_{CC} \pm = \pm 5\text{ V}$ to $\pm 15\text{ V}$, $R_S = 50\Omega$	25°C	75	93		dB	
			Full range	65				
I_{CC}	Supply current	$V_O = 0$, No load	25°C	280	325		μA	
			Full range		350			
			Full range	29				
ΔI_{CC}	Supply-current change over operating temperature range							

† Full range is $-40^\circ C$ to $85^\circ C$.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ C$ extrapolated to $T_A = 25^\circ C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



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operating characteristics at specified free-air temperature, $V_{CC} \pm = \pm 5$ V (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T_A^\dagger	TLE2161I, TLE2161AI TLE2161BI			UNIT
			MIN	TYP	MAX	
SR	Slew rate (see Figure 1) $A_{VD} = 5$, $R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	25°C	7	10		$\text{V}/\mu\text{s}$
		Full range	5			
V_n	Equivalent input noise voltage (see Figure 2) $R_S = 20 \Omega$, $f = 10 \text{ Hz}$ $R_S = 20 \Omega$, $f = 1 \text{ kHz}$	25°C	59	100		$\text{nV}/\sqrt{\text{Hz}}$
			43	60		
$V_{n(PP)}$	Peak-to-peak equivalent input noise voltage $f = 0.1 \text{ Hz to } 10 \text{ Hz}$	25°C	1.1			μV
I_n	Equivalent input noise current $f = 1 \text{ kHz}$	25°C	1			$\text{fA}/\sqrt{\text{Hz}}$
THD	Total harmonic distortion $V_{O(PP)} = 2 \text{ V}$, $A_{VD} = 5$, $f = 10 \text{ kHz}$, $R_L = 10 \text{ k}\Omega$	25°C	0.025%			
	Gain-bandwidth product (see Figure 3) $f = 100 \text{ kHz}$, $R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$ $f = 100 \text{ kHz}$, $R_L = 100 \Omega$, $C_L = 100 \text{ pF}$	25°C	5.8			MHz
			4.3			
t_s	Settling time $\epsilon = 0.1\%$ $\epsilon = 0.01\%$	25°C	5			μs
			10			
B_{OM}	Maximum output-swing bandwidth $A_{VD} = 5$, $R_L = 10 \text{ k}\Omega$	25°C	420			kHz
ϕ_m	Phase margin (see Figure 3) $A_{VD} = 5$, $R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$ $A_{VD} = 5$, $R_L = 100 \Omega$, $C_L = 100 \text{ pF}$	25°C	70°			
			84°			

† Full range is -40°C to 85°C .

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electrical characteristics at specified free-air temperature, $V_{CC} = \pm 15$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A^\dagger	TLE2161I, TLE2161AI TLE2161BI			UNIT	
				MIN	TYP	MAX		
V_{IO}	Input offset voltage	$V_{IC} = 0$, $R_S = 50\Omega$	25°C	0.6	3		mV	
			Full range		4.3			
			25°C	0.5	1.5			
	TLE2161AI		Full range		2.9			
			25°C	0.3	0.5			
			Full range		1.3			
	αV_{IO} Temperature coefficient of input offset voltage		Full range	6		$\mu\text{V}/^\circ\text{C}$		
			25°C	0.04		$\mu\text{V}/\text{mo}$		
			25°C	2		pA		
	Input offset current		Full range		3	nA		
			25°C	4		pA		
			Full range		5	nA		
V_{ICR}	Common-mode input voltage range		25°C	-11 to 13	-12 to 16	V	V	
			Full range	-11 to 13		V		
			$R_L = 10\text{ k}\Omega$	25°C	13.2	13.7		
			Full range	13				
			$R_L = 600\Omega$	25°C	12.5	13.2		
			Full range	12				
			$R_L = 10\text{ k}\Omega$	25°C	-13.2	-13.7		
			Full range	-13				
			$R_L = 600\Omega$	25°C	-12.5	-13		
			Full range	-12				
A_{VD}	Large-signal differential voltage amplification	$V_0 = \pm 10\text{ V}, R_L = 10\text{ k}\Omega$	25°C	30	230		V/mV	
			Full range	20				
			$V_0 = 0$ to $8\text{ V}, R_L = 600\Omega$	25°C	25	100		
			Full range	10				
			$V_0 = 0$ to $-8\text{ V}, R_L = 600\Omega$	25°C	3	25		
		$V_O = 0$, No load	Full range	1				
			25°C		10 ¹²	Ω		
			25°C		4	pF		
			25°C		280	Ω		
			25°C	72	90			
CMRR	Common-mode rejection ratio	$V_{IC}=V_{ICR\text{min}}, R_S = 50\Omega$	Full range	65			dB	
			25°C	75	93			
			Full range	65				
			25°C	290	350			
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm} / \Delta V_{IO}$)	$V_{CC\pm} = \pm 5\text{ V to } \pm 15\text{ V}, R_S = 50\Omega$	Full range	375			dB	
			25°C					
			Full range	34				
ΔI_{CC}	Supply-current change over operating temperature range		25°C				μA	
			Full range					

† Full range is -40°C to 85°C .

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS
 SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

operating characteristics at specified free-air temperature, $V_{CC} = \pm 15$ V (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T_A^\dagger	TLE2161I, TLE2161AI TLE2161IB			UNIT		
			MIN	TYP	MAX			
			25°C	7	10			
SR	Slew rate (see Figure 1) $A_{VD} = 5$, $R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$	Full range	5			$\text{V}/\mu\text{s}$		
V_n	Equivalent input noise voltage (see Figure 2) $R_S = 20\text{ }\Omega$, $f = 10\text{ Hz}$ $R_S = 20\text{ }\Omega$, $f = 1\text{ kHz}$	25°C	70	100	40	$\text{nV}/\sqrt{\text{Hz}}$		
$V_{n(PP)}$	Peak-to-peak equivalent input noise voltage	25°C	1.1			μV		
I_n	Equivalent input noise current	25°C	1.1			$\text{fA}/\sqrt{\text{Hz}}$		
THD	Total harmonic distortion	$V_{O(PP)} = 2\text{ V}$, $A_{VD} = 5$, $f = 10\text{ kHz}$, $R_L = 10\text{ k}\Omega$	25°C	0.025%				
	Gain-bandwidth product (see Figure 3) $f = 100\text{ kHz}$, $R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$ $f = 100\text{ kHz}$, $R_L = 600\text{ }\Omega$, $C_L = 100\text{ pF}$	25°C	6.4		5.6	MHz		
t_s	Settling time $\epsilon = 0.1\%$ $\epsilon = 0.01\%$	25°C	5		10	μs		
B_{OM}	Maximum output-swing bandwidth	$A_{VD} = 5$, $R_L = 10\text{ k}\Omega$	25°C	116				
Φ_m	Phase margin (see Figure 3) $A_{VD} = 5$, $R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$ $A_{VD} = 5$, $R_L = 600\text{ }\Omega$, $C_L = 100\text{ pF}$	25°C	72°		78°			

† Full range is –40°C to 85°C.



**TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS**

SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

electrical characteristics at specified free-air temperature, $V_{CC} \pm = \pm 5$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A^\dagger	TLE2161M TLE2161AM TLE2161BM			UNIT
				MIN	TYP	MAX	
V_{IO}	Input offset voltage			25°C	0.8	3.1	mV
				Full range		6	
				25°C	0.6	2.6	
				Full range		4.6	
				25°C	0.5	1.9	
				Full range		3.1	
αV_{IO}	Temperature coefficient of input offset voltage	$V_{IC} = 0$, $R_S = 50\Omega$		Full range		6	$\mu\text{V}/^\circ\text{C}$
	Input offset voltage long-term drift (see Note 4)			25°C		0.04	$\mu\text{V}/\text{mo}$
I_{IO}	Input offset current			25°C		1	pA
				Full range		15	nA
I_{IB}	Input bias current			25°C		3	pA
				Full range		30	nA
V_{ICR}	Common-mode input voltage range			25°C	-1.6 to 4	-2 to 6	V
				Full range	-1.6 to 4		V
$V_{OM} +$	Maximum positive peak output voltage swing	All packages	$R_L = 10\text{ k}\Omega$	25°C	3.5	3.7	V
				Full range	3		
		FK and JG packages	$R_L = 600\Omega$	25°C	2.5	3.6	V
				Full range	2		
		D and P packages	$R_L = 100\Omega$	25°C	2.5	3.1	
				Full range	2		
$V_{OM} -$	Maximum negative peak output voltage swing	All packages	$R_L = 10\text{ k}\Omega$	25°C	-3.7	-3.9	V
				Full range	-3		
		FK and JG packages	$R_L = 600\Omega$	25°C	-2.5	-3.5	
				Full range	-2		
		D and P packages	$R_L = 100\Omega$	25°C	-2.5	-2.7	
				Full range	-2		
AVD	Large-signal differential voltage amplification	All packages	$V_0 = \pm 2.8\text{ V}$, $R_L = 10\text{ k}\Omega$	25°C	15	80	V/mV
				Full range	2		
		FK and JG packages	$V_0 = 0$ to 2.5 V , $R_L = 600\Omega$	25°C	1	65	
				Full range	0.5		
				25°C	1	16	
				Full range	0.5		
		D and P packages	$V_0 = 0$ to 2 V , $R_L = 100\Omega$	25°C	0.75	45	
				Full range	0.5		
			$V_0 = 0$ to -2 V , $R_L = 100\Omega$	25°C	0.5	3	
				Full range	0.25		

† Full range is -55°C to 125°C .

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS
 SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

electrical characteristics at specified free-air temperature, $V_{CC \pm} = \pm 5$ V (unless otherwise noted continued)

PARAMETER	TEST CONDITIONS	T_A^{\dagger}	TLE2161M TLE2161AM TLE2161BM			UNIT
			MIN	TYP	MAX	
r_i	Input resistance	25°C	10 ¹²			Ω
c_i	Input capacitance	25°C	4			pF
z_o	Open-loop output impedance	$I_O = 0$	25°C	280		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR\min}, R_S = 50 \Omega$	25°C	65	82	dB
			Full range	60		
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC \pm}/\Delta V_{IO}$)	$V_{CC \pm} = \pm 5$ V to ± 15 V, $R_S = 50 \Omega$	25°C	75	93	dB
			Full range	65		
I_{CC}	Supply current	$V_O = 0$, No load	25°C	280	325	μA
			Full range		350	
ΔI_{CC}	Supply-current change over operating temperature range		Full range		39	μA

[†] Full range is –55°C to 125°C.

operating characteristics, $V_{CC \pm} = \pm 5$ V, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	TLE2161M TLE2161AM TLE2161BM			UNIT
		MIN	TYP	MAX	
SR	Slew rate (see Figure 1)	A/D = 5, $R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	10		V/μs
V_n	Equivalent input noise voltage (see Figure 2)	$R_S = 20 \Omega$, $f = 10 \text{ Hz}$	59		nV/√Hz
		$R_S = 20 \Omega$, $f = 1 \text{ kHz}$	43		
$V_n(\text{PP})$	Peak-to-peak equivalent input noise voltage	$f = 0.1 \text{ Hz to } 10 \text{ Hz}$	1.1		μV
I_n	Equivalent input noise current	$f = 1 \text{ kHz}$	1		fA/√Hz
THD	Total harmonic distortion	A/D = 5, $V_O(\text{PP}) = 2 \text{ V}$, $f = 10 \text{ kHz}$, $R_L = 10 \text{ k}\Omega$	0.025%		
	Gain-bandwidth product (see Figure 3)	$f = 100 \text{ kHz}$, $R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	5.8		MHz
		$f = 100 \text{ kHz}$, $R_L = 600 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	4.3		
t_s	Settling time	$\varepsilon = 0.1\%$	5		μs
		$\varepsilon = 0.01\%$	10		
B_{OM}	Maximum output-swing bandwidth	A/D = 5, $R_L = 10 \text{ k}\Omega$	420		kHz
ϕ_m	Phase margin (see Figure 3)	A/D = 5, $R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	70°		
		A/D = 5, $R_L = 600 \Omega$, $C_L = 100 \text{ pF}$	84°		

**TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS**

SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

electrical characteristics at specified free-air temperature, $V_{CC} \pm \pm 15$ V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A^\dagger	TLE2161M TLE2161AM TLE2161BM			UNIT	
				MIN	TYP	MAX		
V_{IO}	Input offset voltage	$V_{IC} = 0$, $R_S = 50\Omega$	25°C	0.6	3		mV	
			Full range		6			
			25°C	0.5	1.5			
	TLE2161AM		Full range		3.6			
			25°C	0.3	0.5			
			Full range		1.7			
α_{VIO}	Temperature coefficient of input offset voltage		Full range		6	$\mu\text{V}/^\circ\text{C}$		
Input offset voltage long-term drift (see Note 4)			25°C	0.04		$\mu\text{V}/\text{mo}$		
I_{IO}	Input offset current		25°C	2		pA		
			Full range		20	nA		
			25°C	4		pA		
			Full range		40	nA		
V_{ICR}	Common-mode input voltage range		25°C	-11 to 13	-12 to 16	V		
			Full range	-11 to 13		V		
$V_{OM} +$	Maximum positive peak output voltage swing	$R_L = 10\text{ k}\Omega$	25°C	13.2	13.7		V	
			Full range	12.5				
		$R_L = 600\Omega$	25°C	12.5	13.2			
			Full range	12				
$V_{OM} -$	Maximum negative peak output voltage swing	$R_L = 10\text{ k}\Omega$	25°C	-13.2	-13.7		V	
			Full range	-12.5				
		$R_L = 600\Omega$	25°C	-12.5	-13			
			Full range	-12				
A_{VD}	Large-signal differential voltage amplification	$V_O = \pm 10\text{ V}, R_L = 10\text{ k}\Omega$	25°C	30	230		V/mV	
			Full range	20				
		$V_O = 0 \text{ to } 8\text{ V}, R_L = 600\Omega$	25°C	25	100			
			Full range	7				
		$V_O = 0 \text{ to } -8\text{ V}, R_L = 600\Omega$	25°C	3	25			
			Full range	1				
r_i	Input resistance		25°C		10 ¹²	Ω		
c_i	Input capacitance		25°C		4	pF		
Z_o	Open-loop output impedance	$I_O = 0$	25°C		280	Ω		
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR\min}, R_S = 50\Omega$	25°C	72	90		dB	
			Full range	65				
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm} / \Delta V_{IO}$)	$V_{CC\pm} = \pm 5\text{ V to } \pm 15\text{ V}, R_S = 50\Omega$	25°C	75	93		dB	
			Full range	65				
I_{CC}	Supply current	$V_O = 0$, No load	25°C		290	350	μA	
			Full range			375		
	Supply-current change over operating temperature range		Full range		46			

† Full range is -55°C to 125°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS
 SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

operating characteristics at specified free-air temperature, $V_{CC} \pm = \pm 15$ V (unless otherwise noted)

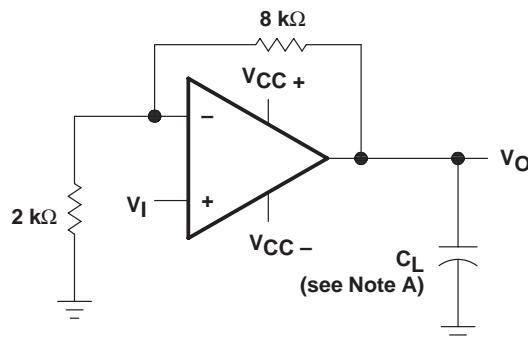
PARAMETER	TEST CONDITIONS	T_A^\dagger	TLE2161M			UNIT		
			TLE2161AM					
			TLE2161BM					
SR	Slew rate (see Figure 1) $A_{VD} = 5$, $R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	25°C	7	10		$\text{V}/\mu\text{s}$		
		Full range	5					
V_n	Equivalent input noise voltage (see Figure 2) $R_S = 20 \Omega$, $f = 10 \text{ Hz}$	25°C	70	40	$\text{nV}/\sqrt{\text{Hz}}$			
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage $f = 0.1 \text{ Hz to } 10 \text{ Hz}$	25°C	1.1			μV		
I_n	Equivalent input noise current $f = 1 \text{ Hz}$	25°C	1.1			$\text{fA}/\sqrt{\text{Hz}}$		
THD	Total harmonic distortion $V_{O(PP)} = 2 \text{ V}$, $A_{VD} = 5$, $f = 10 \text{ kHz}$, $R_L = 10 \text{ k}\Omega$	25°C	0.025%					
	Gain-bandwidth product (see Figure 3) $f = 100 \text{ kHz}$, $R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	25°C	6.4			MHz		
			5.6					
t_s	Settling time $\varepsilon = 0.1\%$	25°C	5			μs		
			10					
BOM	Maximum output-swing bandwidth $A_{VD} = 5$, $R_L = 10 \text{ k}\Omega$	25°C	116			kHz		
ϕ_m	Phase margin (see Figure 3) $A_{VD} = 5$, $R_L = 10 \text{ k}\Omega$, $C_L = 100 \text{ pF}$	25°C	72°					
			78°					

† Full range is -55°C to 125°C .

**TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS**

SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

PARAMETER MEASUREMENT INFORMATION



NOTE A: C_L includes fixture capacitance.

Figure 1. Slew-Rate Test Circuit

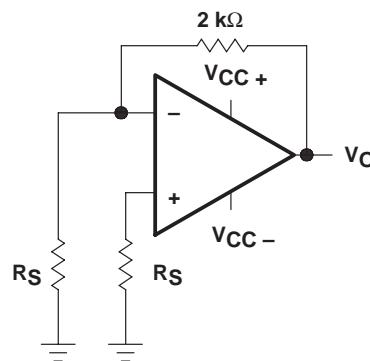
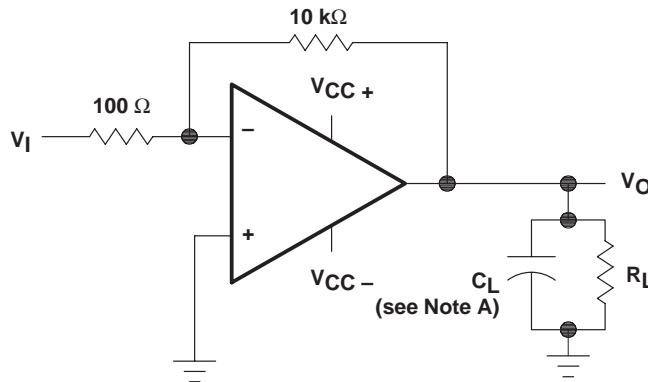


Figure 2. Noise-Voltage Test Circuit



NOTE A: C_L includes fixture capacitance.

Figure 3. Gain-Bandwidth Product and Phase-Margin Test Circuit

typical values

Typical values presented in this data sheet represent the median (50% point) of device parametric performance.

Input bias and offset current

At the picoampere bias-current level typical of the TLE2161, TLE2161A, and TLE2161B, accurate measurement of the bias current becomes difficult. Not only does this measurement require a picoammeter, but test socket leakages can easily exceed the actual device bias currents. To accurately measure these small currents, Texas Instruments uses a two-step process. The socket leakage is measured using picoammeters with bias voltages applied but with no device in the socket. The device is then inserted into the socket, and a second test that measures both the socket leakage and the device input bias current is performed. The two measurements are then subtracted algebraically to determine the bias current of the device.

TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS
 SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

TYPICAL CHARACTERISTICS

Table of Graphs

		FIGURE
V_{IO}	Input offset voltage	Distribution 4
I_{IB}	Input bias current	vs Common-mode input voltage 5 vs Free-air temperature 6
I_{IO}	Input offset current	vs Free-air temperature 6
V_{ICR}	Common-mode input voltage range limits	vs Free-air temperature 7
V_{OM}	Maximum positive peak output voltage	vs Output current 8
V_{OM}	Maximum negative peak output voltage	vs Output current 9
V_{OM}	Maximum peak output voltage	vs Supply voltage 10, 11, 12
$V_{O(PP)}$	Maximum peak-to-peak output voltage	vs Frequency 13, 14, 15
AVD	Large-signal differential voltage amplification	vs Frequency 16 vs Free-air temperature 17
I_{OS}	Short-circuit output current	vs Elapsed time 18
	Large-signal voltage amplification	vs Free-air temperature 19
z_o	Output impedance	vs Frequency 20
$CMRR$	Common-mode rejection ratio	vs Frequency 21
I_{CC}	Supply current	vs Supply voltage 22 vs Free-air temperature 23
	Pulse response	Small signal 24, 25 Large signal 26, 27
	Noise voltage (referred to input)	0.1 to 10 Hz 28
V_n	Equivalent input noise voltage	vs Frequency 29
THD	Total harmonic distortion	vs Frequency 30, 31
	Gain-bandwidth product	vs Supply voltage 32 vs Free-air temperature 33
ϕ_m	Phase margin	vs Supply voltage 34 vs Free-air temperature 35
	Phase shift	vs Frequency 16

**TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS**

SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

TYPICAL CHARACTERISTICS†

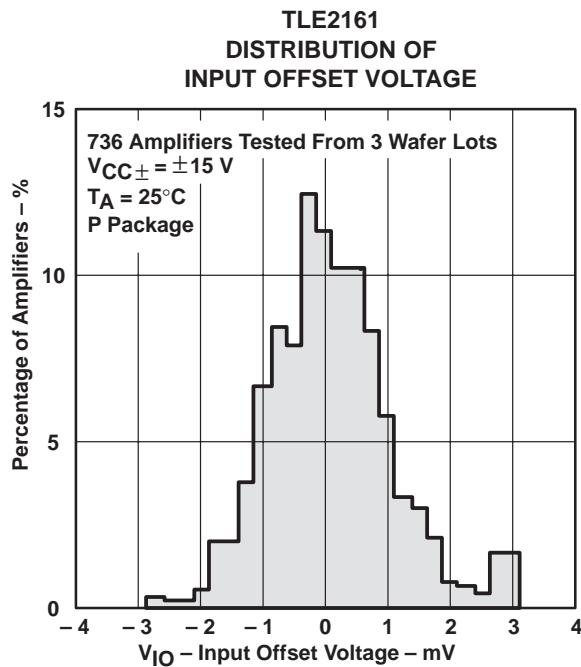


Figure 4

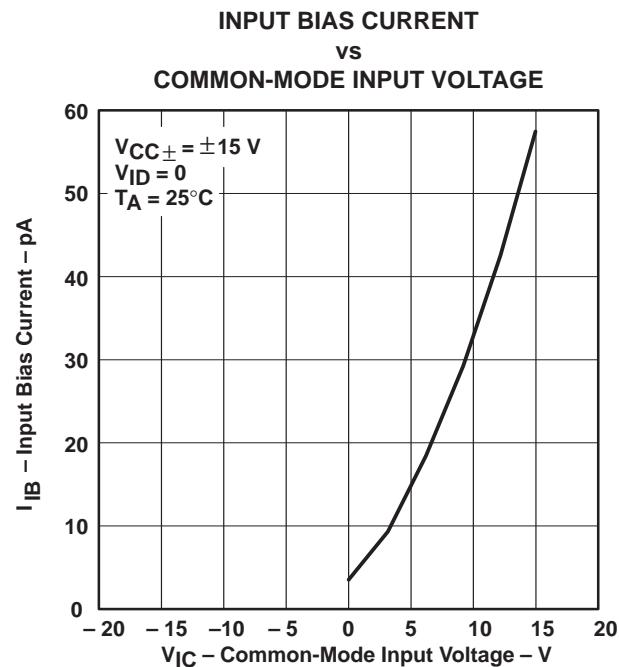


Figure 5

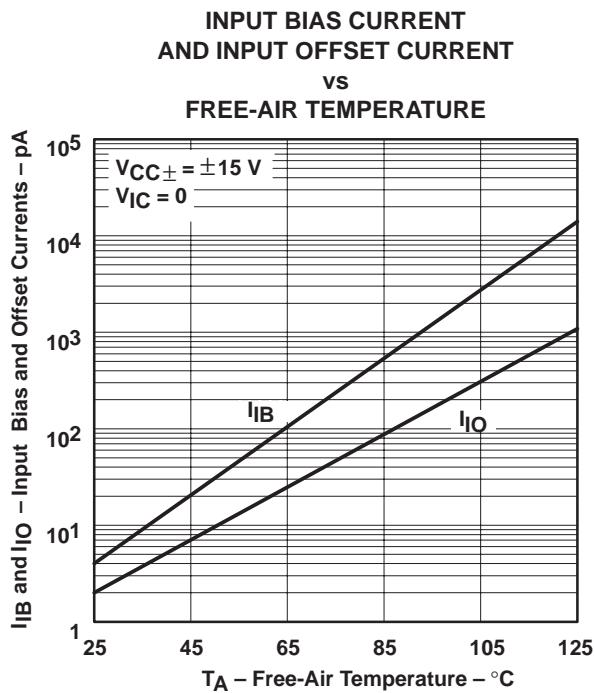


Figure 6

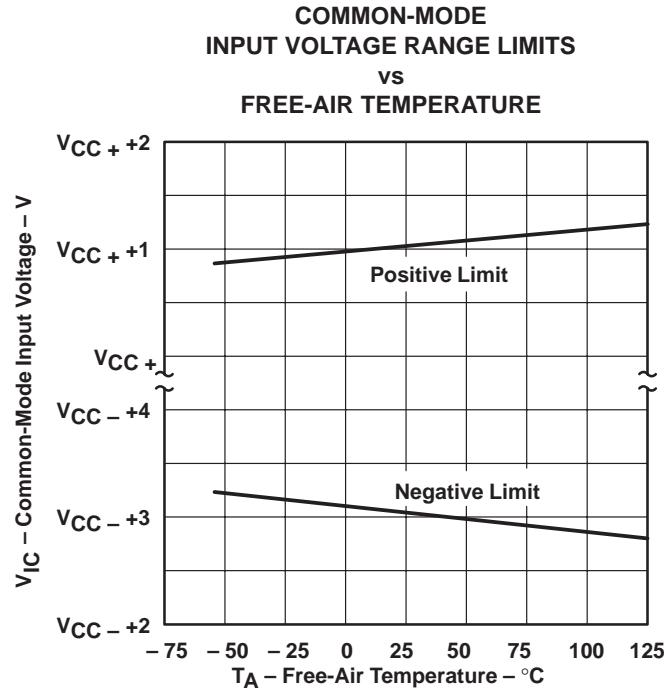


Figure 7

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

**MAXIMUM POSITIVE PEAK
OUTPUT VOLTAGE
vs
OUTPUT CURRENT**

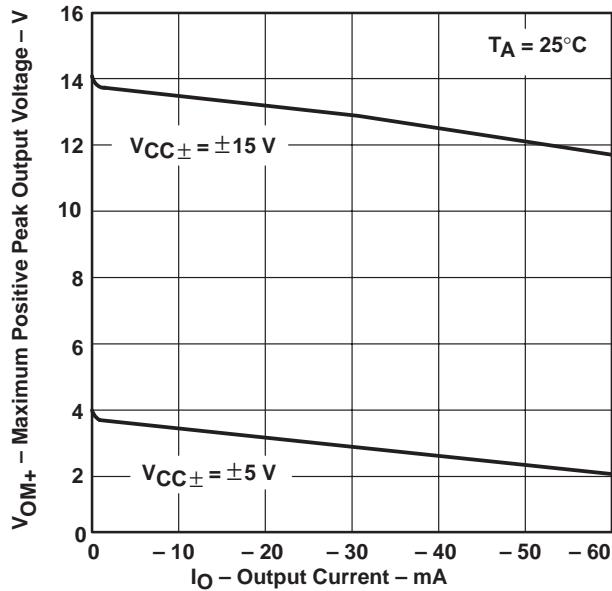


Figure 8

**MAXIMUM NEGATIVE PEAK
OUTPUT VOLTAGE
vs
OUTPUT CURRENT**

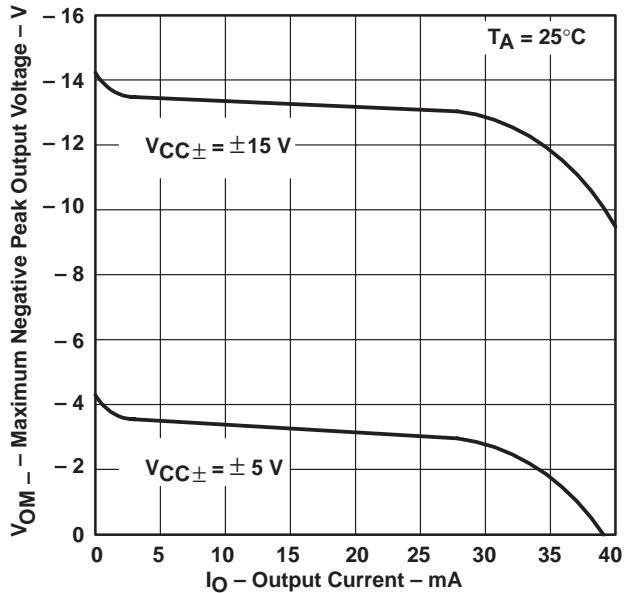


Figure 9

**MAXIMUM PEAK OUTPUT VOLTAGE
vs
SUPPLY VOLTAGE**

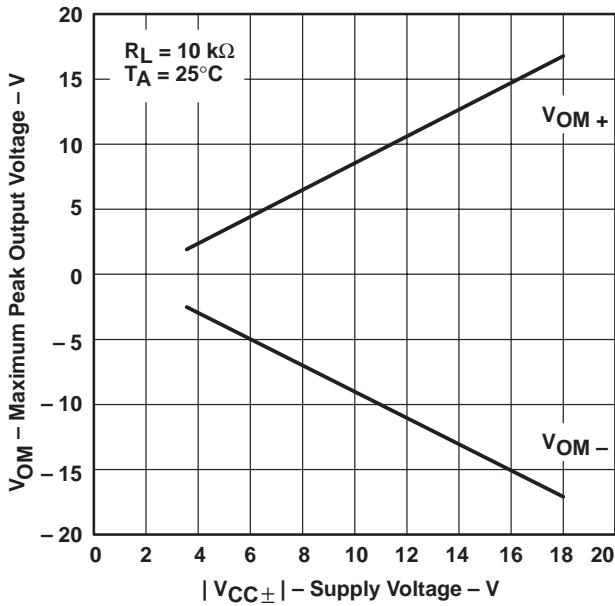


Figure 10

**MAXIMUM PEAK OUTPUT VOLTAGE
vs
SUPPLY VOLTAGE**

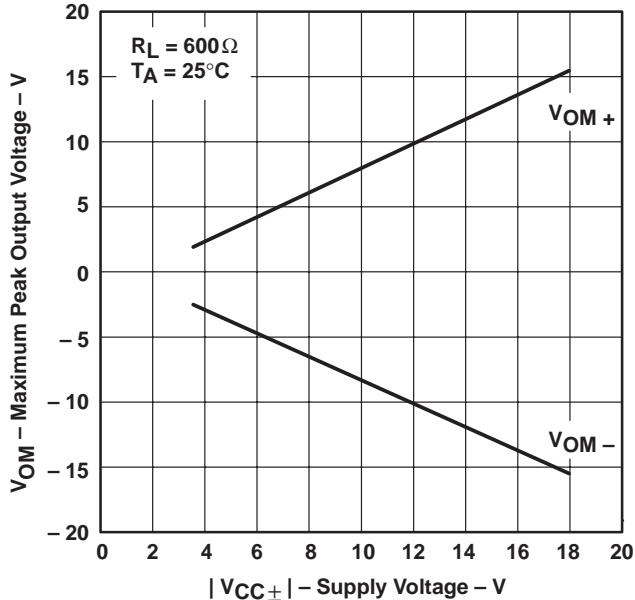


Figure 11

**TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS**

SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

TYPICAL CHARACTERISTICS

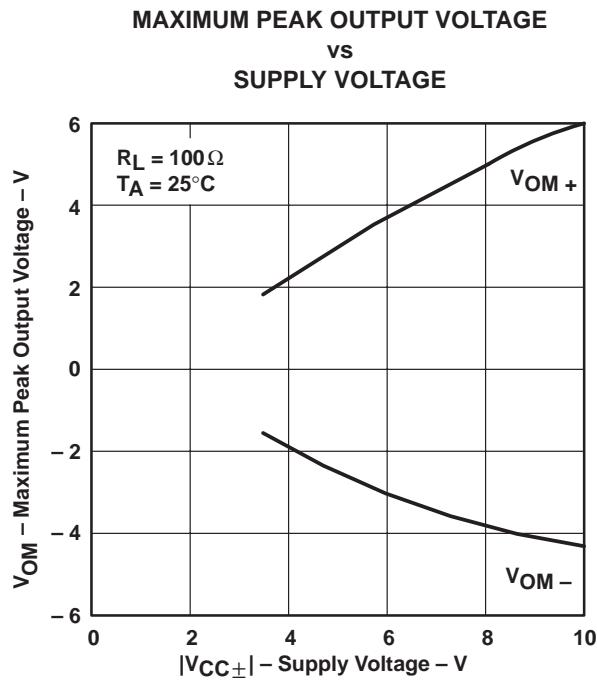


Figure 12

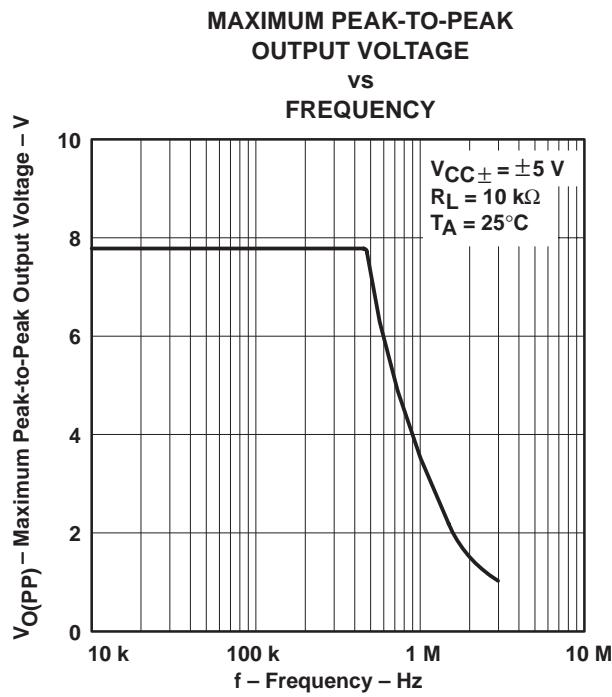


Figure 13

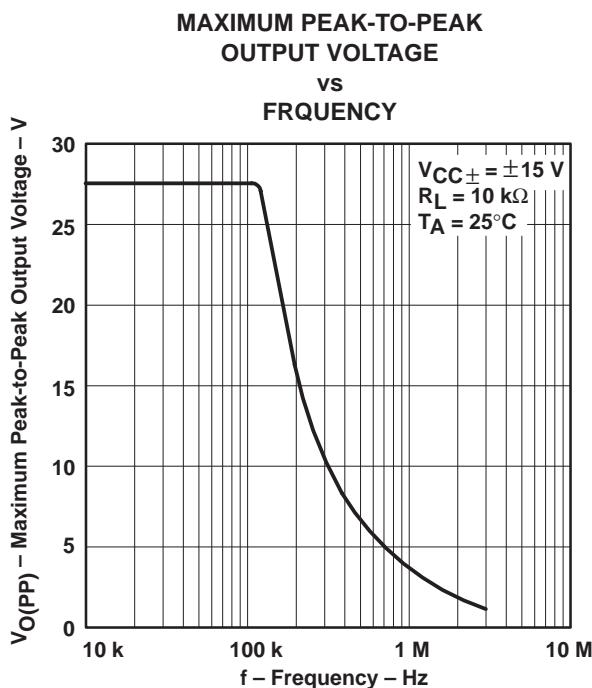


Figure 14

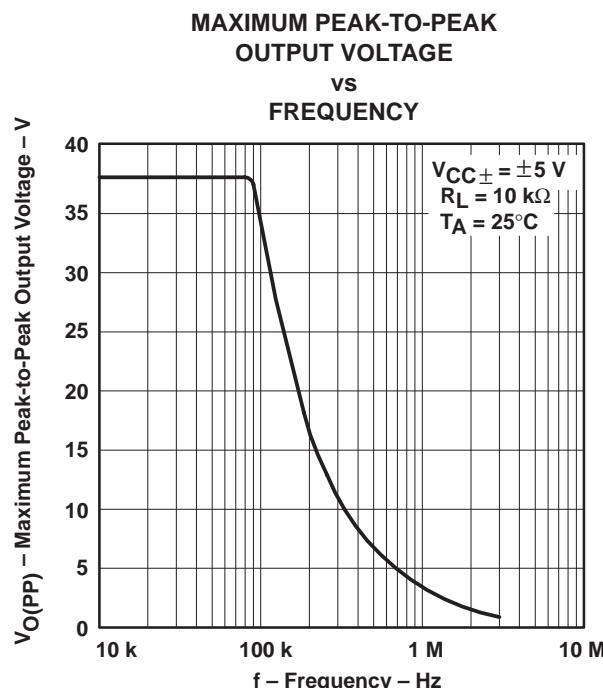


Figure 15

TYPICAL CHARACTERISTICS[†]

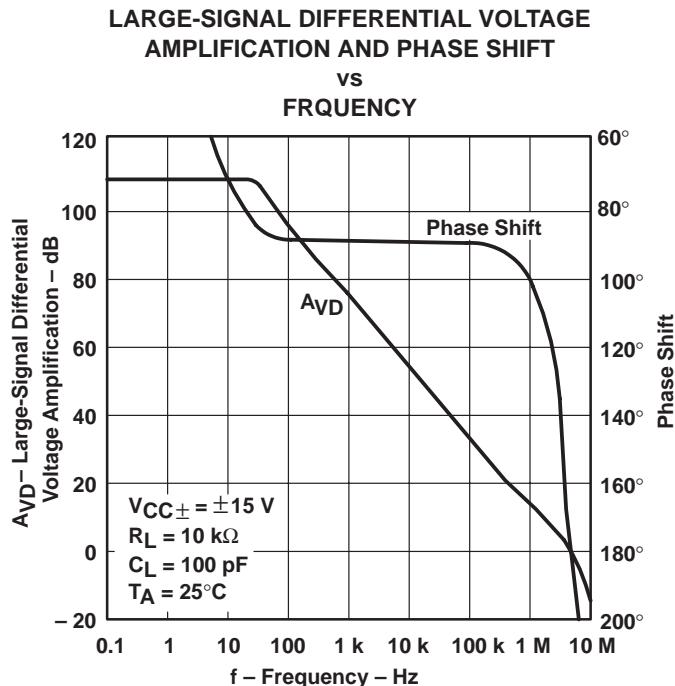


Figure 16

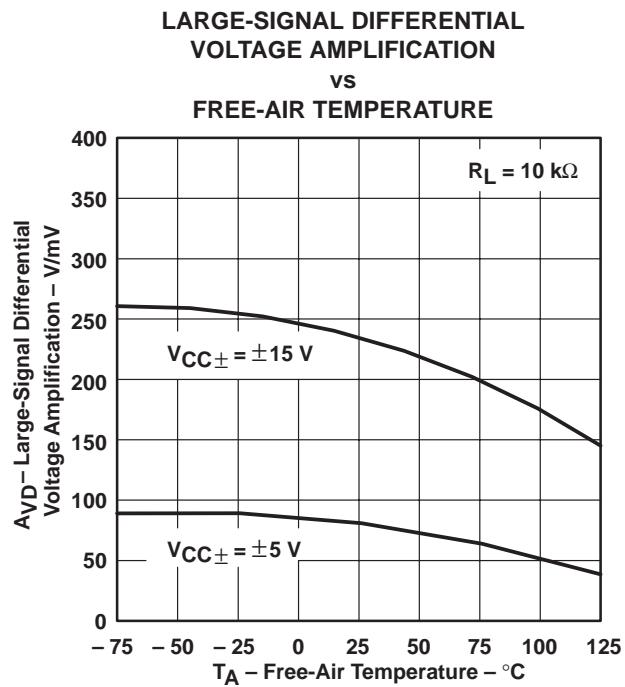


Figure 17

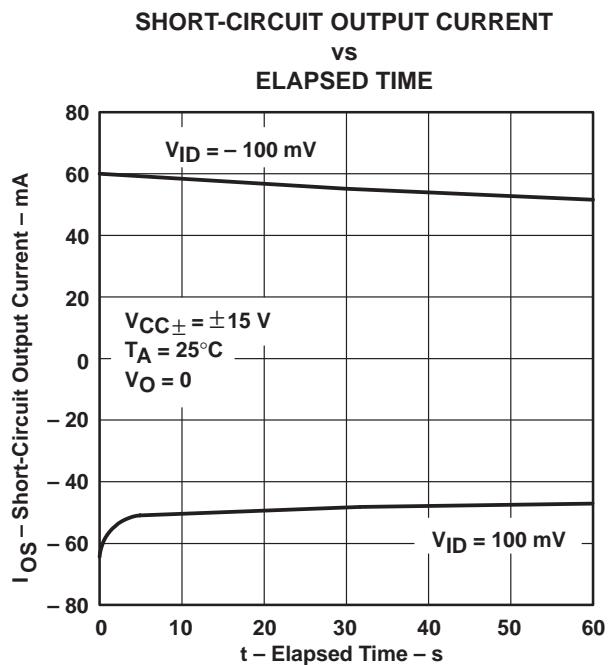


Figure 18

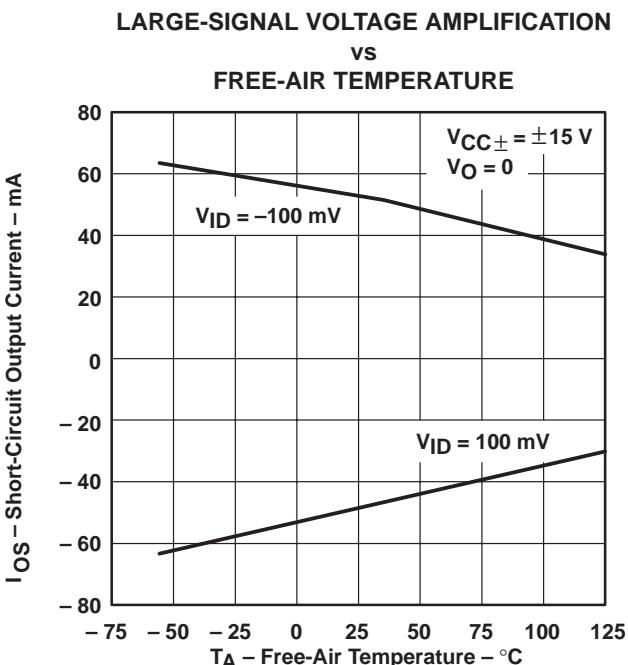


Figure 19

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

**TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS**

SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

TYPICAL CHARACTERISTICS†

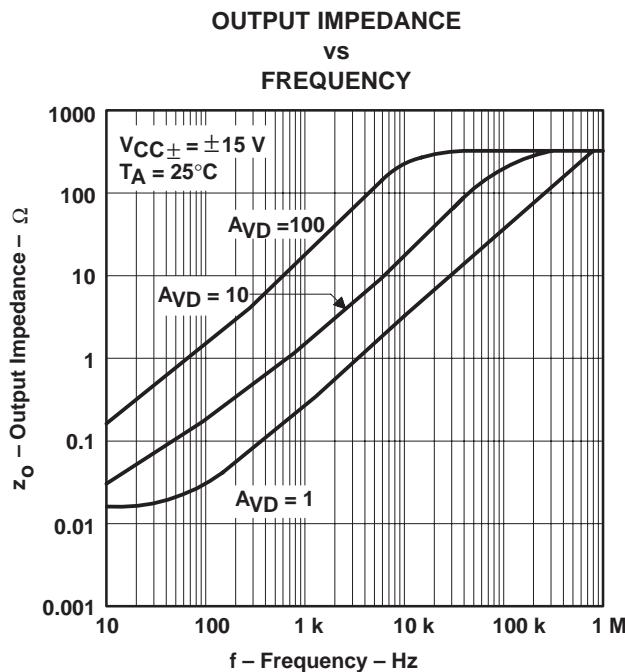


Figure 20

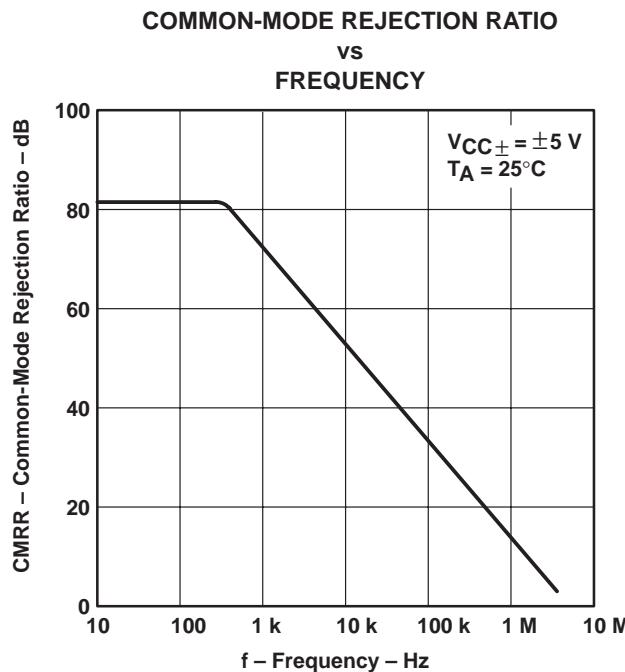


Figure 21

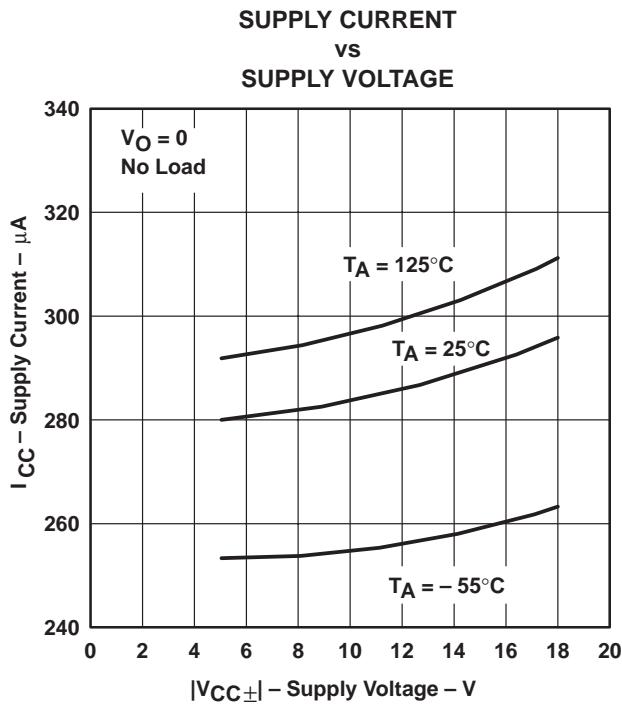


Figure 22

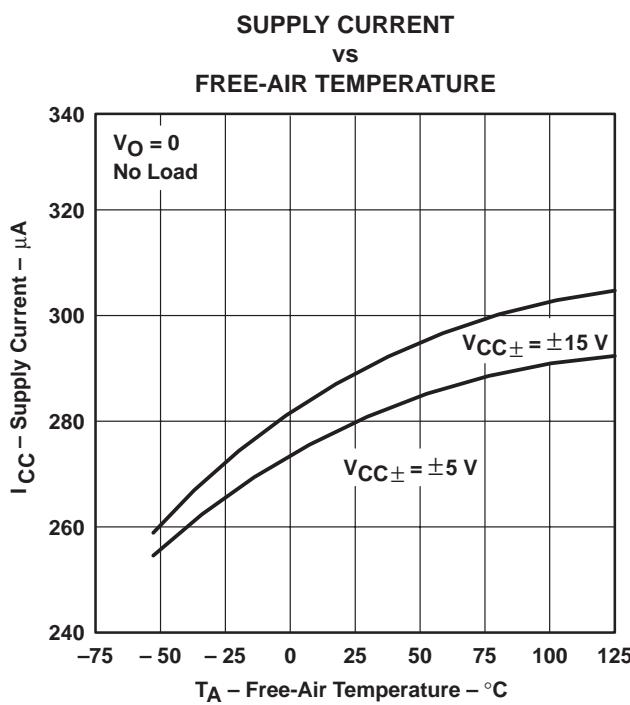


Figure 23

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

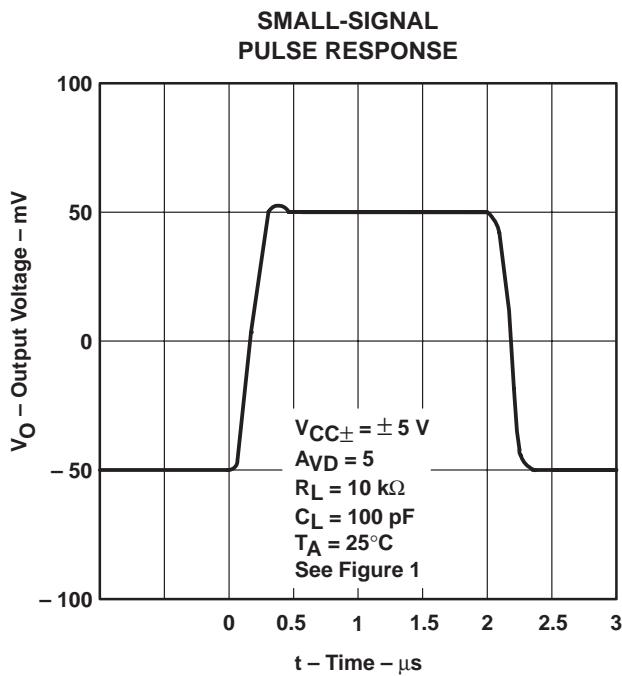


Figure 24

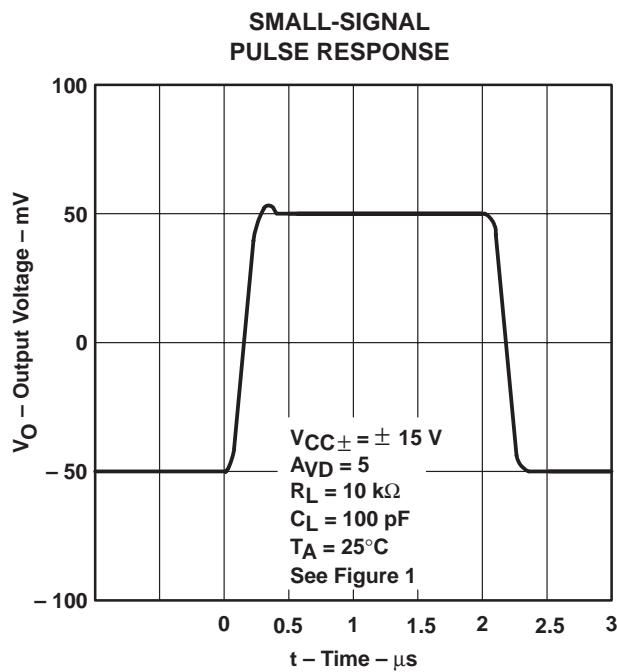


Figure 25

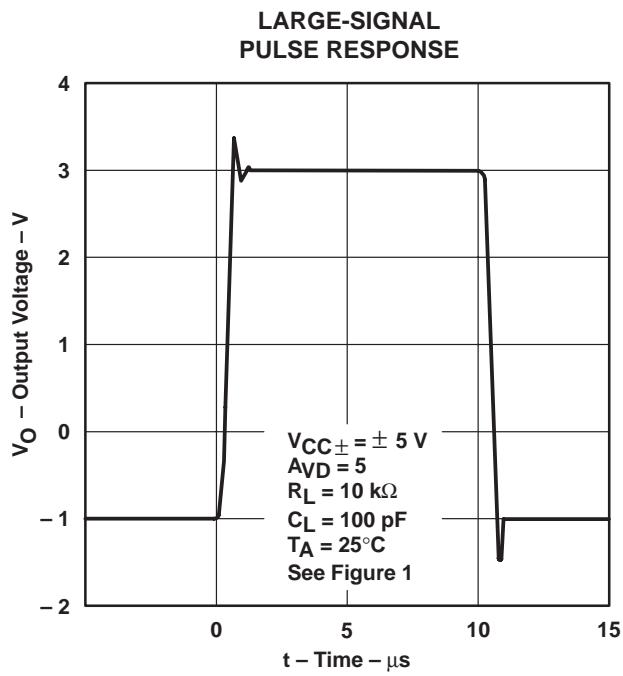


Figure 26

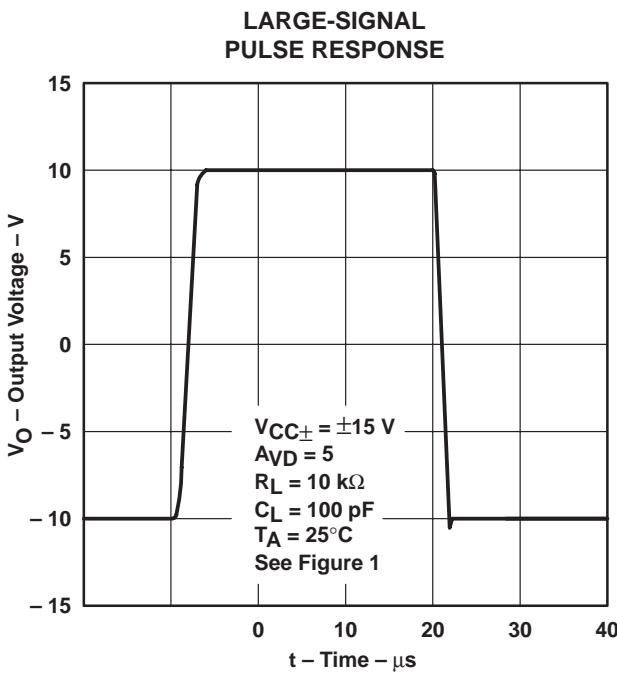


Figure 27

**TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS**

SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

TYPICAL CHARACTERISTICS

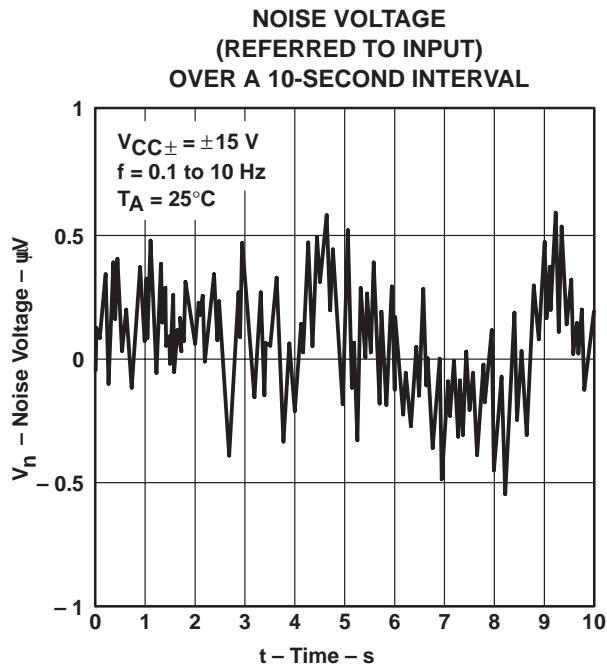


Figure 28

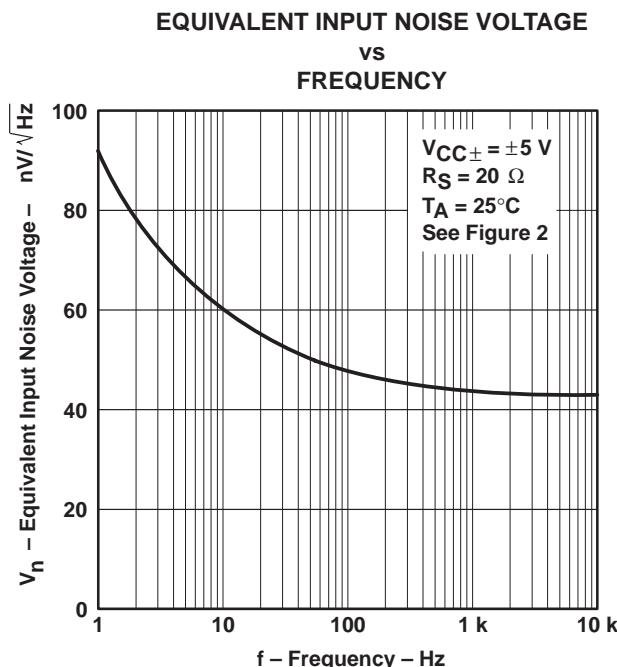


Figure 29

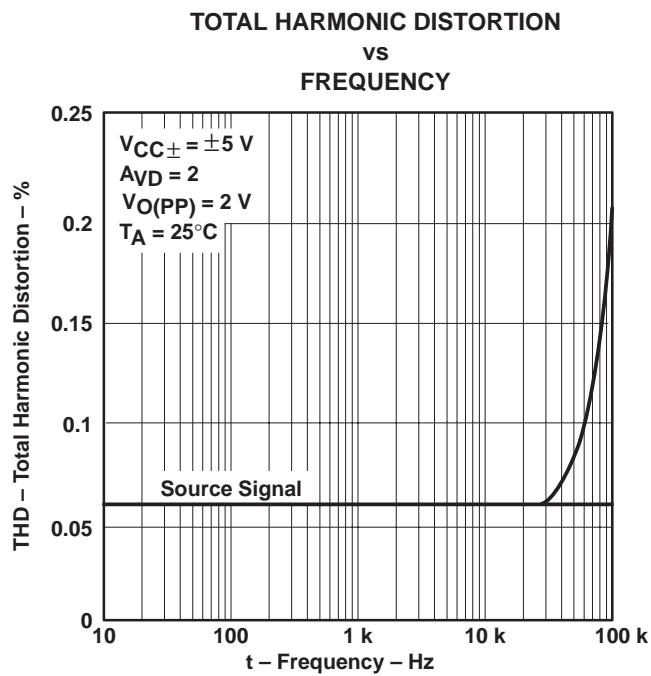


Figure 30

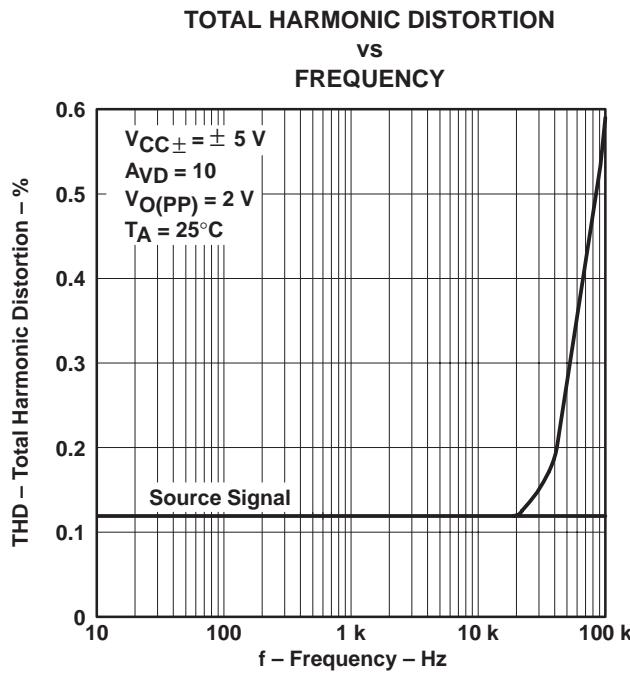


Figure 31

TYPICAL CHARACTERISTICS

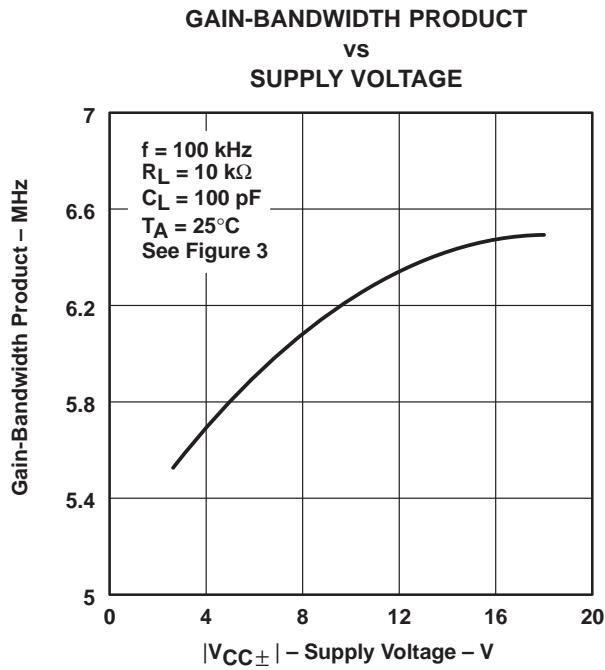


Figure 32

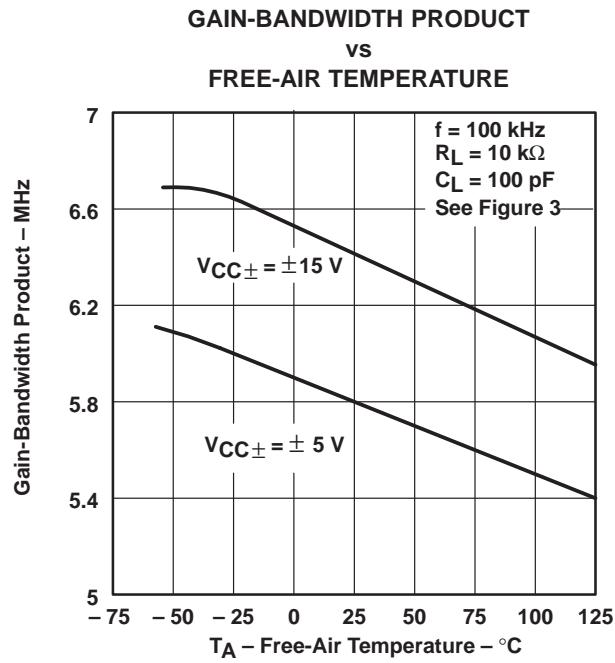


Figure 33

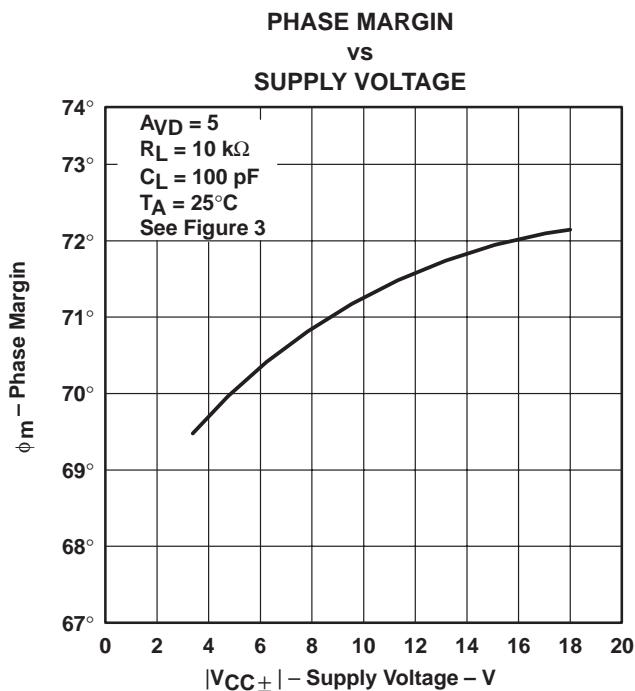


Figure 34

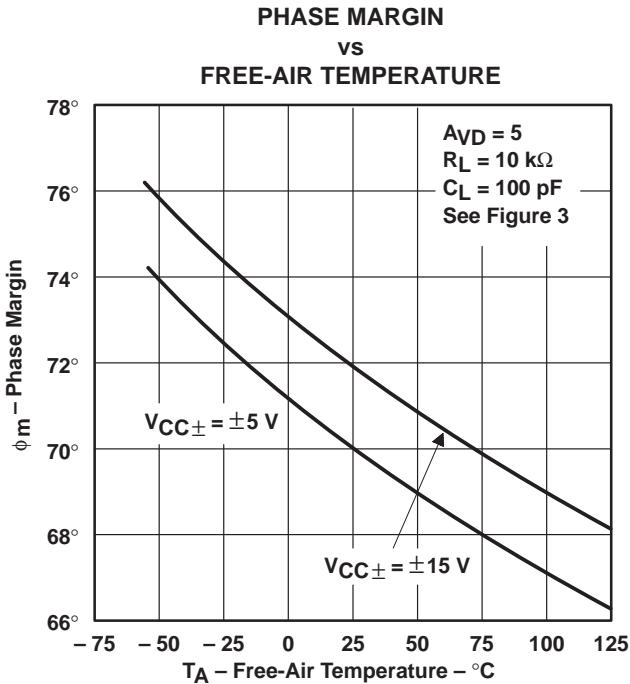


Figure 35

**TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS**

SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

APPLICATION INFORMATION

macromodel information

Macromodel information provided was derived using Microsim *Parts*™, the model generation software used with Microsim *PSpice*™. The Boyle macromodel (see Note 5) and subcircuit in Figure 36 and Figure 37 were generated using the TLE2161 typical electrical and operating characteristics at 25°C. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Gain-bandwidth product
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

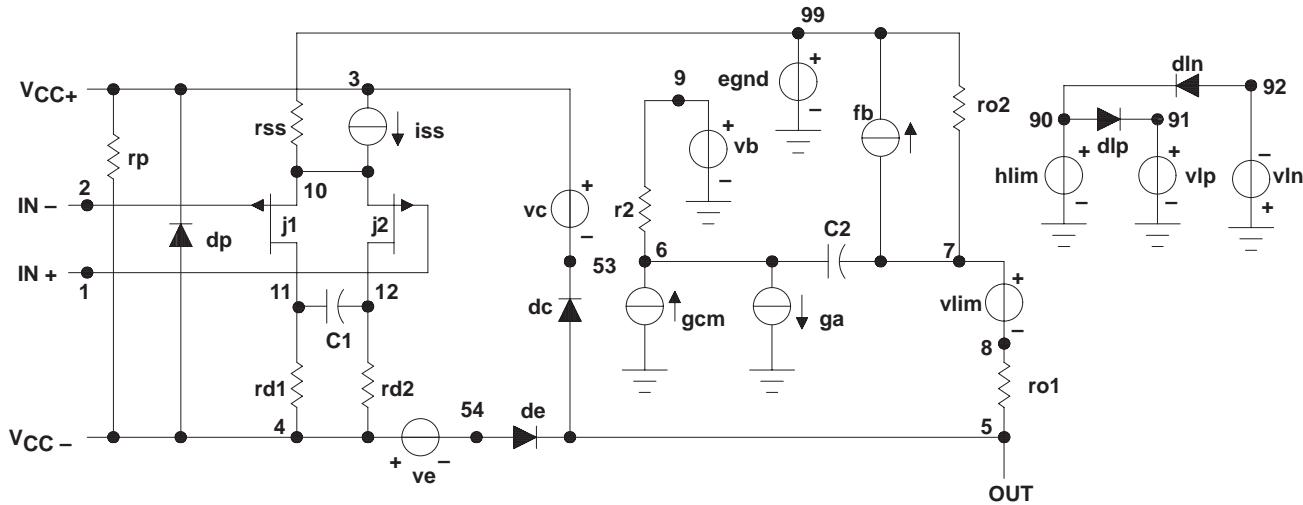


Figure 36. Boyle Macromodel

NOTE 5: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers", *IEEE Journal of Solid-State Circuits*, SC-9, 353 (1974).

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APPLICATION INFORMATION

macromodel information (continued)

```
.subckt TLE2161 1 2 3 4 5
c1    11 12 125.4E-14
c2     6  7 5.000E-12
dc     5  53 dx
de    54 5d x
dlp   90  91 dx
dln   92  90 dx
dp     4  3 dx
egnd  99  0 poly(2) (3,0) (4,0) 0 .5 .5
fb     7  99 poly(5) vb vc ve vlp vln 0 4.085E6 -4E6 4E6 4E6 -4E6
ga     6  0 11 12 201.1E-6
gcm    0  6 10 99 3.576E-9
iss    3  10 dc 45.00E-6
hlim   90  0 vlim 1K
j1     11  2 10 jx
j2     12  1 10 jx
r2     6  9 100.0E3
rd1    4  11 4.973E3
rd2    4  12 4.973E3
rol    8  5 280
ro2    7  99 280
rp     3  4 113.2E3
rss   10  99 4.444E6
vb     9  0 dc 0
vc     3  53 dc 2
ve     54  4 dc 2
vlim   7  8 dc 0
vlp    91  0 dc 50
vln    0  92 dc 50
.model dx D (Is=800.0E-18)
.model jx PJF (Is=1.000E-12 Beta=480E-6 Vto=-1)
.ends
```

Figure 37. Macromodel Subcircuit

**TLE2161, TLE2161A, TLE2161B
EXCALIBUR JFET-INPUT HIGH-OUTPUT-DRIVE
μPOWER OPERATIONAL AMPLIFIERS**

SLOS049D – NOVEMBER 1989 – REVISED MAY 1996

APPLICATION INFORMATION

input characteristics

The TLE2161, TLE2161A and TLE2161B are specified with a minimum and a maximum input voltage that if exceeded at either input could cause the device to malfunction.

Because of the extremely high input impedance and resulting low bias-current requirements, the TLE2161, TLE2161A, and TLE2161B are well suited for low-level signal processing; however, leakage currents on printed circuit boards and sockets can easily exceed bias-current requirements and cause degradation in system performance. It is a good practice to include guard rings around inputs (see Figure 38). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input.

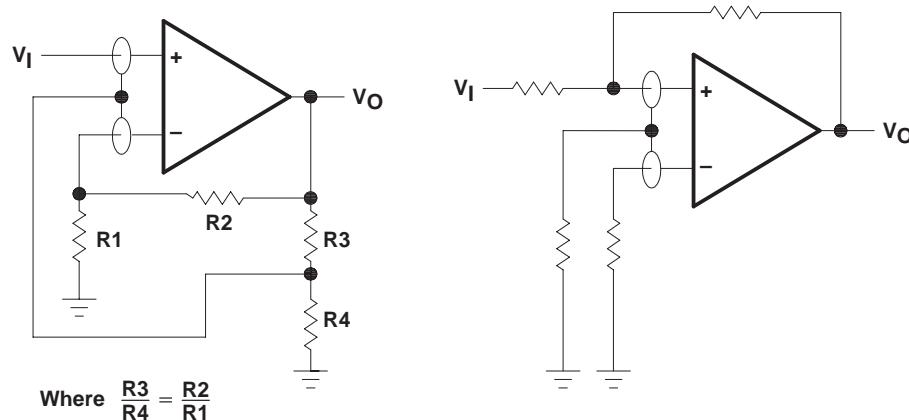


Figure 38. Use of Guard Rings

input offset voltage nulling

The TLE2161 series offers external null pins that can further reduce the input offset voltage. The circuit in Figure 39 can be connected as shown if the feature is desired. When external nulling is not needed, the null pins may be left disconnected.

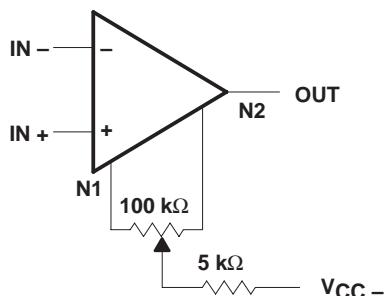


Figure 39. Input Offset Voltage Nulling

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
5962-9095801Q2A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
5962-9095801QPA	ACTIVE	CDIP	JG	8	1	TBD	A42 SNPB	N / A for Pkg Type
5962-9095802Q2A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
5962-9095802QPA	ACTIVE	CDIP	JG	8	1	TBD	A42 SNPB	N / A for Pkg Type
5962-9095803Q2A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
5962-9095803QPA	ACTIVE	CDIP	JG	8	1	TBD	A42 SNPB	N / A for Pkg Type
TLE2161ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2161ACDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2161ACP	OBsolete	PDIP	P	8		TBD	Call TI	Call TI
TLE2161AID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2161AIDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2161AIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2161AIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2161AIP	OBsolete	PDIP	P	8		TBD	Call TI	Call TI
TLE2161AMFKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
TLE2161AMJGB	ACTIVE	CDIP	JG	8	1	TBD	A42 SNPB	N / A for Pkg Type
TLE2161BCP	OBsolete	PDIP	P	8		TBD	Call TI	Call TI
TLE2161BIP	OBsolete	PDIP	P	8		TBD	Call TI	Call TI
TLE2161BMFKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
TLE2161BMJG	ACTIVE	CDIP	JG	8	1	TBD	A42 SNPB	N / A for Pkg Type
TLE2161BMJGB	ACTIVE	CDIP	JG	8	1	TBD	A42 SNPB	N / A for Pkg Type
TLE2161BMP	OBsolete	PDIP	P	8		TBD	Call TI	Call TI
TLE2161CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2161CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2161CP	OBsolete	PDIP	P	8		TBD	Call TI	Call TI
TLE2161ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2161IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2161IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2161IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2161IP	OBsolete	PDIP	P	8		TBD	Call TI	Call TI
TLE2161MFKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
TLE2161MJGB	ACTIVE	CDIP	JG	8	1	TBD	A42 SNPB	N / A for Pkg Type
TLE2161MP	OBsolete	PDIP	P	8		TBD	Call TI	Call TI

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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